

+175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

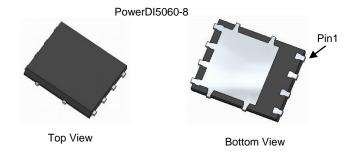
| BVDSS | R _{DS(ON)} Max | Qg Typ | I _D T _C = +25°C |
|-------|-------------------------------|--------|--|
| 40V | 2.7mΩ @ V _{GS} = 10V | 68.6nC | 100A |

Description and Applications

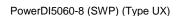
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

Site 1:



Site 2:









Bottom View

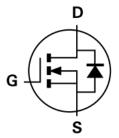
Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4004SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

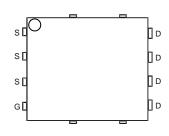
https://www.diodes.com/quality/product-definitions/

Mechanical Data

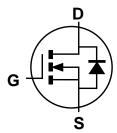
- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



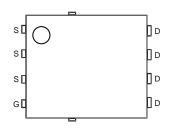
Internal Schematic



Top View Pin Configuration



Internal Schematic



Top View Pin Configuration

Ordering Information (Note 4)

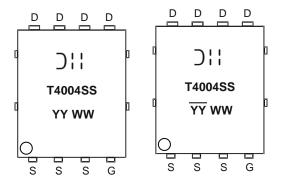
| Part Number | Package | Packing | | |
|-----------------|-------------------------------|---------|-------------|--|
| Fait Nullibei | rackage | Qty. | Carrier | |
| DMTH4004SPSQ-13 | PowerDI5060-8 | 2,500 | Tape & Reel | |
| DMTH4004SPSQ-13 | PowerDI5060-8 (SWP) (Type UX) | 2,500 | Tape & Reel | |

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



☐ → Substitute →

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|---|-------------------------------------|-----------|----------|----|
| Drain-Source Voltage | VDSS | 40 | V | |
| Gate-Source Voltage | | V_{GSS} | ±20 | V |
| Continuous Drain Current (Note 5) | $T_A = +25$ °C $T_A = +70$ °C | ID | 31 26 | А |
| | Tc = +25°C | lo | 100 | А |
| Continuous Drain Current (Note 6) | T _C = +100°C (Note 8) | | 100 | |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | 350 | Α | |
| Maximum Continuous Body Diode Forward Current (Note 5) | Is | 100 | Α | |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%) | | lsм | 350 | Α |
| Avalanche Current, L=0.2mH | | las | 45 | Α |
| Avalanche Energy, L=0.2mH | | Eas | 200 | mJ |

Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|---|------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | T _A = +25°C | PD | 3.6 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | | Reja | 41 | °C/W |
| Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$ | | P _D | 167 | W |
| Thermal Resistance, Junction to Case (Note 6) | | Rejc | 0.9 | °C/W |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +175 | °C |

Notes: 5. Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single- sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady state.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

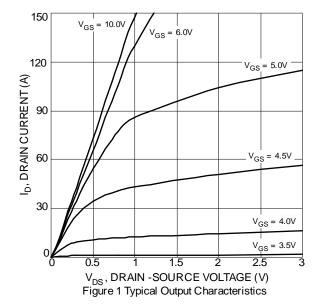
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|------------------------------------|---------------------|-----|-------|------|------|---|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | • | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 40 | _ | _ | V | $V_{GS} = 0V$, $I_D = 1mA$ | |
| Zero Gate Voltage Drain Current | IDSS | _ | _ | 1 | μΑ | V _{DS} = 32V, V _{GS} = 0V | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±100 | nA | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | Vgs(TH) | 2 | _ | 4 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | _ | 2.3 | 2.7 | mΩ | $V_{GS} = 10V, I_{D} = 90A$ | |
| Diode Forward Voltage | VsD | _ | 0.9 | 1.2 | V | V _G S = 0V, I _S = 20A | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | Ciss | _ | 4,305 | _ | pF | V _{DS} = 25V, V _{GS} = 0V, f = 1MHz | |
| Output Capacitance | Coss | _ | 1,441 | _ | | | |
| Reverse Transfer Capacitance | Crss | _ | 102 | | | | |
| Gate Resistance | Rg | _ | 0.77 | _ | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge | Qg | _ | 68.6 | _ | | V _{DD} = 20V, I _D = 90A, V _{GS} = 10V | |
| Gate-Source Charge | Qgs | _ | 16.8 | _ | nC | | |
| Gate-Drain Charge | Q_{gd} | _ | 14.2 | _ | | | |
| Turn-On Delay Time | t _{D(ON)} | _ | 9.5 | _ | | $V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$ | |
| Turn-On Rise Time | t _R | _ | 6.7 | _ | | | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 26.4 | _ | ns | | |
| Turn-Off Fall Time | t _F | _ | 8.1 | _ | | | |
| Body Diode Reverse Recovery Time | trr | _ | 52.4 | _ | ns | I- 504 di/dt 4004/:- | |
| Body Diode Reverse Recovery Charge | Qrr | _ | 78.2 | _ | nC | I _F = 50A, di/dt = 100A/μs | |

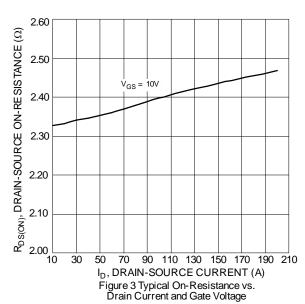
Notes:

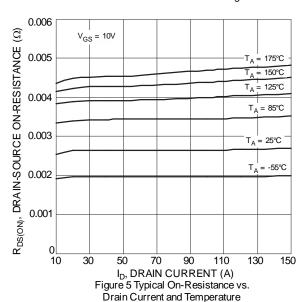
^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing

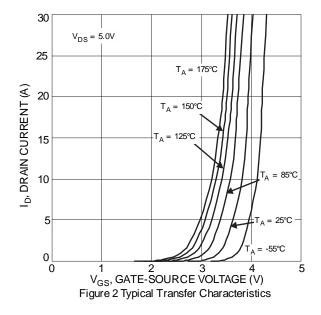


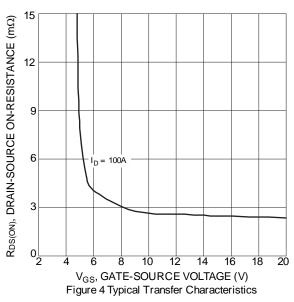


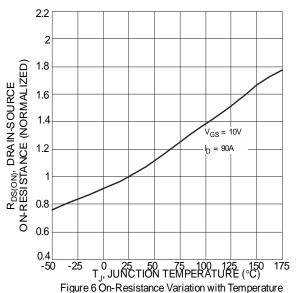






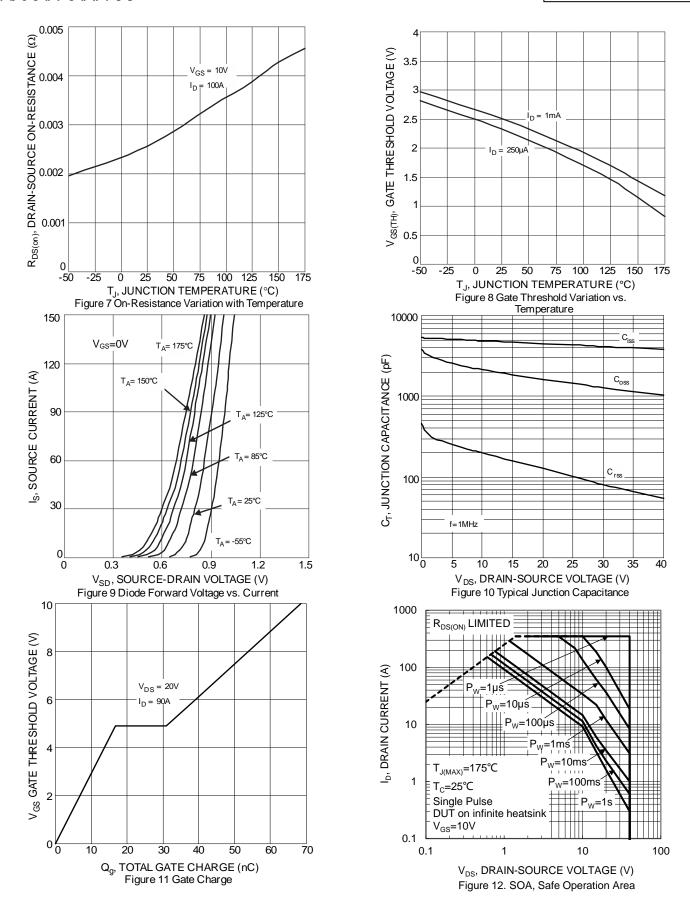














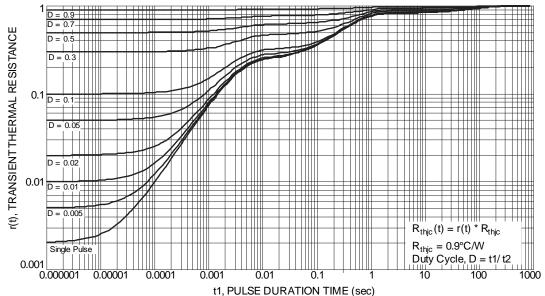


Figure 13 Transient Thermal Resistance

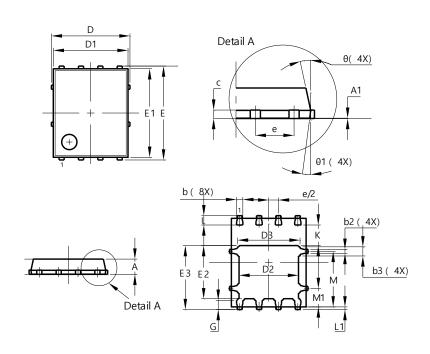


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

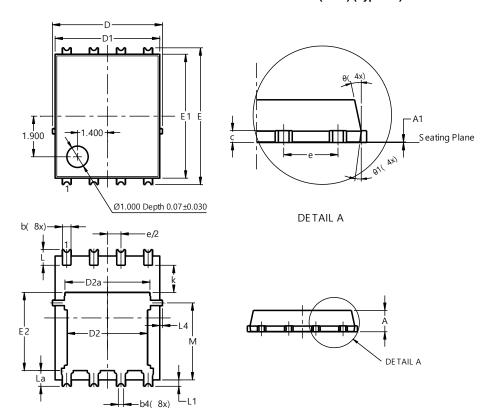
PowerDI5060-8



| PowerDI5060-8 | | | | |
|----------------------|----------|----------|-------|--|
| Dim | Min | Max | Тур | |
| Α | 0.90 | 1.10 | 1.00 | |
| A1 | 0.00 | 0.05 | - | |
| b | 0.33 | 0.51 | 0.41 | |
| b2 | 0.200 | 0.350 | 0.273 | |
| b3 | 0.40 | 0.80 | 0.60 | |
| C D | 0.230 | 0.330 | 0.277 | |
| | ļ | 5.15 BSC | ; | |
| D1 | 4.70 | 5.10 | 4.90 | |
| D2 | 3.70 | 4.10 | 3.90 | |
| D3 | 3.90 | 4.30 | 4.10 | |
| Е | 6.15 BSC | | | |
| E1 | 5.60 | 6.00 | 5.80 | |
| E2 | 3.28 | 3.68 | 3.48 | |
| E3 | 3.99 | 4.39 | 4.19 | |
| е | 1.27 BSC | | | |
| G | 0.51 | 0.71 | 0.61 | |
| K | 0.51 | - | - | |
| L | 0.51 | 0.71 | 0.61 | |
| L1 | 0.100 | 0.200 | 0.175 | |
| M | 3.235 | 4.035 | 3.635 | |
| M1 | 1.00 | 1.40 | 1.21 | |
| Θ | 10° | 12° | 11° | |
| Θ1 | 6° | 8° | 7° | |
| All Dimensions in mm | | | | |

Site 2:

PowerDI5060-8 (SWP) (Type UX)



| PowerDI5060-8 (SWP) (Type UX) | | | | | |
|----------------------------------|----------|---------|-------|--|--|
| | | | | | |
| Dim | Min | Max | Тур | | |
| Α | 0.90 | 1.10 | 1.00 | | |
| A 1 | 0 | 0.05 | | | |
| b | 0.30 | 0.50 | 0.41 | | |
| b2 | 0.20 | 0.35 | 0.25 | | |
| b4 | (|).25REF | - | | |
| С | 0.230 | 0.330 | 0.277 | | |
| D | 5 | .15 BS0 |) | | |
| D1 | 4.70 | 5.10 | 4.90 | | |
| D2 | 3.56 | 3.96 | 3.76 | | |
| D2a | 3.78 | 4.18 | 3.98 | | |
| Е | 6.40 BSC | | | | |
| E1 | 5.60 | 6.00 | 5.80 | | |
| E2 | 3.46 | 3.86 | 3.66 | | |
| E2a | 4.195 | 4.595 | 4.395 | | |
| е | 1 | .27BSC | | | |
| k | 1.05 | | | | |
| L | 0.635 | 0.835 | 0.735 | | |
| La | 0.635 | 0.835 | 0.735 | | |
| L1 | 0.200 | 0.400 | 0.300 | | |
| L1a | 0 | .050RE | F | | |
| L4 | 0.025 | 0.225 | 0.125 | | |
| М | 3.205 | 4.005 | 3.605 | | |
| θ | 10° | 12° | 11° | | |
| θ1 | 6° | 8° | 7° | | |
| All Dimensions in mm | | | | | |
| | | | | | |

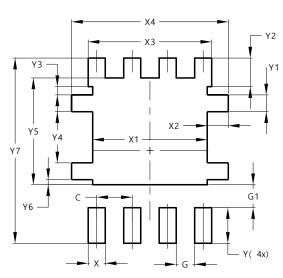


Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

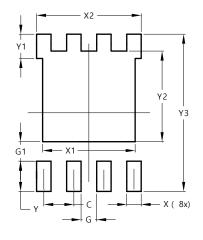
PowerDI5060-8



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 1.270 |
| G | 0.660 |
| G1 | 0.820 |
| X | 0.610 |
| X1 | 4.100 |
| X2 | 0.755 |
| Х3 | 4.420 |
| X4 | 5.610 |
| Y | 1.270 |
| Y1 | 0.600 |
| Y2 | 1.020 |
| Y3 | 0.295 |
| Y4 | 1.825 |
| Y5 | 3.810 |
| Y6 | 0.180 |
| Y7 | 6.610 |
| | |

Site 2:

PowerDI5060-8 (SWP) (Type UX)



| Dimensions | Value | |
|---------------|---------|--|
| Dillielisions | (in mm) | |
| С | 1.270 | |
| G | 0.660 | |
| G1 | 0.820 | |
| Х | 0.610 | |
| X1 | 4.100 | |
| X2 | 4.420 | |
| Υ | 1.270 | |
| Y1 | 1.020 | |
| Y2 | 3.810 | |
| Y3 | 6.610 | |



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